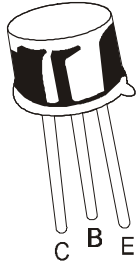


NPN SILICON PLANAR EPITAXIAL TRANSISTORS

**2N3019
2N3020**



**TO-39
Metal Can Package**

**Designed for use in General Purpose Amplifier and High Speed Switching Applications
These Transistors are also Suitable for High Current Amplifier Applications**

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V_{CEO}	80	V
Collector Base Voltage	V_{CBO}	140	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current	I_{CM}	1	A
Power Dissipation @ Ta=25° C	P_D	800	mW
Power Dissipation @ Tc=25°C		5	W
Junction Temperature	T_j	+200	°C
Storage Temperature	T_{stg}	-65 to +200	°C
THERMAL RESISTANCE			
Junction to Ambient	$R_{th(j-a)}$	218.7	°C/W
Junction to Case	$R_{th(j-c)}$	35	°C/W

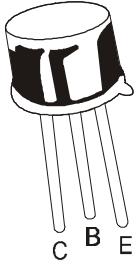
ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Collector Emitter Breakdown Voltage	BV_{CEO}^*	$I_C=30mA, I_B=0$	80		V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	140		V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	7		V
Collector Leakage Current	I_{CBO}	$V_{CB}=90V, I_E=0$		10	nA
		$V_{CB}=90V, I_E=0, T_a=150^\circ C$		10	μA
Emitter Leakage Current	I_{EBO}	$V_{EB}=5V, I_C=0$		10	nA
Collector Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C=150mA, I_B=15mA$		0.2	V
		$I_C=500mA, I_B=50mA$		0.5	V
Base Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C=150mA, I_B=15mA$		1.1	V

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**TO-39
Metal Can Package**



ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

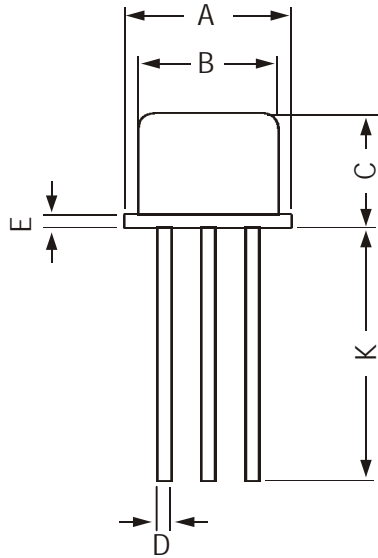
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
DC Current Gain	h_{FE}^*	$I_C=0.1mA, V_{CE}=10V$			
2N3019			50		
2N3020			30	100	
	h_{FE}^*	$I_C=10mA, V_{CE}=10V$			
2N3019			90		
2N3020			40	120	
	h_{FE}^*	$I_C=150mA, V_{CE}=10V$			
2N3019			100	300	
2N3020			40	120	
	h_{FE}^*	$I_C=500mA, V_{CE}=10V$			
2N3019			50		
2N3020			30	100	
	h_{FE}^*	$I_C=1A, V_{CE}=10V$			
2N3019			15		
2N3020			15		
	h_{FE}^*	$I_C=150mA, V_{CE}=10V$ $T_C = -55^\circ C$			
2N3019			40		
SMALL SIGNAL CHARACTERISTICS					
Small Signal Current Gain	$ h_{fe} $	$I_C=1mA, V_{CE}=5V, f=1KHz$			
2N3019			80	400	
2N3020			30	200	
Transition Frequency	f_T	$I_C=50mA, V_{CE}=10V$			
2N3019		$f=20MHz$	100		MHz
2N3020			80		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		12	pF
Input Capacitance	C_{ib}	$V_{EB}=0.5V, I_C=0, f=1MHz$		60	pF
Noise Figure	NF	$I_C=100\mu A, V_{CE}=10V$			
2N3019		$R_s=1K\Omega, f=1KHz$		4	dB
Collector Base Time Constant	$r_{bb'}cb'c$	$I_C=10mA, V_{CB}=10V, f=4MHz$		400	ps
		$f=1MHz$			

*Pulse Test: Pulse Width $\leq 300ms$, Duty Cycle $\leq 1.0\%$

2N3019
2N3020

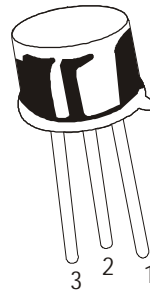
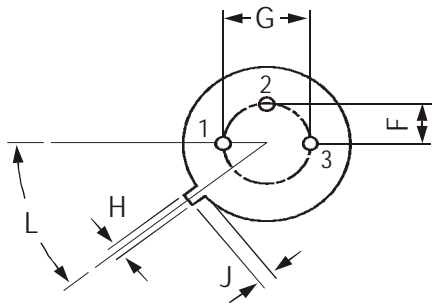
TO-39
Metal Can Package

TO-39 Metal Can Package



DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG

All dimensions are in mm



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

Disclaimer

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